

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	3267102	archive et al .inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/28 08:42
L3	0	(archive.inv.)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/28 09:31
L4	55720	SEM or "scanning electron microscope" and "electron beam" and etch\$4 and (wah or clean) and ("xenon difluoride" or "XeF2") and platinum and tungsten	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/28 09:34
L5	4	(SEM or "scanning electron microscope") and "electron beam" and etch\$4 and (wah or clean) and ("xenon difluoride" or "XeF2") and platinum and tungsten	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/28 09:34
S1	16	((("6507044") or ("6454512") or ("6268608") or ("5986264") or ("5798529") or ("5612535") or ("5481109") or ("4682019"))).PN. or ((2002/0094694) or (2002/0019137)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:49
S2	0	S1 and encapsulant\$4 and polysilicon and metal and (ion near beam) and electron and etch\$4 and gas and (clean or wash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:03
S3	4	encapsulant\$4 and polysilicon and metal and (ion near beam) and electron and etch\$4 and gas and (clean or wash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:10
S4	0	encapsulant\$4 and polysilicon and metal and (ion near beam) and electron and etch\$4 and gas and (clean or wash) and SEM	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:03
S5	0	encapsulant\$4 and polysilicon and metal and (ion near beam) and electron and etch\$4 and gas and (clean or wash) and (scan same microscope)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 14:04
S6	0	encapsulant\$4 and polysilicon and metal and (ion near beam) and electron and etch\$4 and gas and (clean or wash) and scan same microscope	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 14:04

S7	0	encapsulant\$4 and polysilicon and metal and (ion near beam) and electron and etch\$4 and gas and (clean or wash) and microscope	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 14:04
S8	0	encapsulant\$4 near8 polysilicon and metal and (ion near beam) and electron and etch\$4 and gas and (clean or wash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:10
S9	0	(encapsulant\$4 near8 polysilicon) and metal and (ion near beam) and electron and etch\$4 and gas and (clean or wash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:10
S10	4	(encapsulant\$4 near8 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:10
S11	4	(encapsulant\$4 near8 polysilicon) and metal	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:10
S12	0	(encapsulant\$4 near8 polysilicon) and metal and "ion beam"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:11
S13	0	(encapsulant\$4 near8 polysilicon) and metal and (ion near8 beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:11
S14	3	(encapsulant\$4 near8 polysilicon) and metal and beam	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:11
S15	2	(encapsulant\$4 near8 polysilicon) and metal and beam and electron	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:11
S16	2	(encapsulant\$4 near8 polysilicon) and metal and beam and electron and etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:11
S17	2	(encapsulant\$4 near8 polysilicon) and metal and beam and electron and etch\$4 and gas	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:12
S18	0	(encapsulant\$4 near8 polysilicon) and metal and beam and electron and etch\$4 and gas and microscope	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:12

S19	756788	(encapsulant\$4 near8 polysilicon) and metal and beam and electron and etch\$4 and gas an(wash or clean)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:12
S20	0	(encapsulant\$4 near8 polysilicon) and metal and beam and electron and etch\$4 and gas and (wash or clean)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:12
S21	2	(encapsulant\$4 near8 polysilicon) and metal and beam and electron and etch\$4 and gas	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:15
S22	12281	"electron beam" and "ion beam"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:16
S23	0	"electron beam" and "ion beam" and (encapsulant\$4 near8 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:16
S24	9	"electron beam" and "ion beam" and encapsulant\$4 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:17
S25	9	"electron beam" and "ion beam" and encapsulant\$4 and polysilicon and metal	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:17
S26	8	"electron beam" and "ion beam" and encapsulant\$4 and polysilicon and metal and etch\$4 and gas	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:17
S27	4	"electron beam" and "ion beam" and encapsulant\$4 and polysilicon and metal and etch\$4 and gas and (clean or wash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:20
S28	36	"electron beam" and "ion beam" and (metal near8 polysilicon) and etch\$4 and gas and (clean or wash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:20
S29	13	"electron beam" and "ion beam" and (metal near8 polysilicon) and etch\$4 and gas and (clean or wash) and microscope	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:21
S30	4	"electron beam" and "ion beam" and (metal near8 polysilicon) and etch\$4 and gas and (clean or wash) and microscope and scan	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:32

S31	272	"electron beam" and "ion beam" and (metal near8 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:33
S32	49	"electron beam" and "ion beam" and (metal near8 polysilicon) and etch\$4 and (clean or wash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:37
S33	21	"electron beam" and "ion beam" and (metal near8 polysilicon) and etch\$4 and (clean or wash) and microscope	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:37
S34	0	"electron beam" and "ion beam" and (metal near8 polysilicon) and etch\$4 and (clean or wash) and microscope and "xenon difluoride"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:37
S35	10	"electron beam" and "ion beam" and (metal near8 polysilicon) and etch\$4 and (clean or wash) and microscope and platinum	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:38
S36	1	"electron beam" and "ion beam" and (metal near8 polysilicon) and etch\$4 and (clean or wash) and microscope and platinum and tungsten	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/27 14:38
S37	4	(polysilicon near8 metal) and encap\$8 and etch\$4 and "ion beam" and "electron beam" and (clean or wash)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/28 08:38